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### FAIRCHILD

SEMICONDUCTOR

November 2013

### FQD4P25TM\_WS P-Channel QFET<sup>®</sup> MOSFET -250 V, -3.1 A, 2.1 Ω

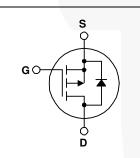
#### Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### Features

- -3.1 A, -250 V,  $R_{DS(on)}$  = 2.1  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = -1.55 A
- Low Gate Charge (Typ. 10 nC)
- Low Crss (Typ. 10.3 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant





#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

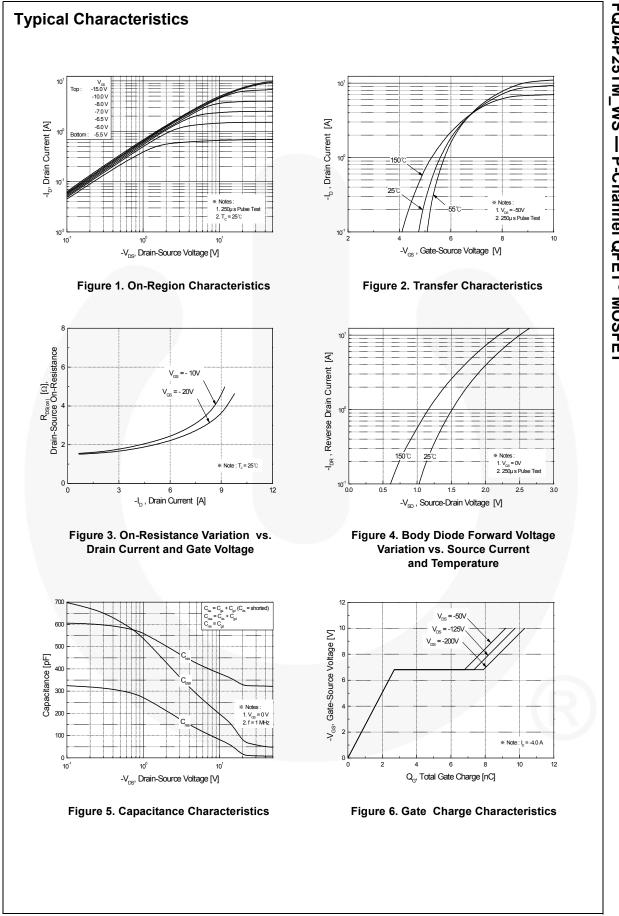
Symbol	Parameter		FQD4P25TM_WS	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		-250	V	
I <sub>D</sub>	Drain Current - Continuous ( $T_c = 25^{\circ}C$ )		-3.1	А	
	- Continuous (T <sub>C</sub> = 100°C)		-1.96	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-12.4	A	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	280	mJ	
I <sub>AR</sub>	Avalanche Current (Note 1)		-3.1	А	
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		4.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-5.5	V/ns	
P <sub>D</sub>	Power Dissipation ( $T_A = 25^{\circ}C$ ) *	2.5	W		
	Power Dissipation ( $T_C = 25^{\circ}C$ )	45	W		
	- Derate above 25°C	0.36	W/°C		
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
Τ <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C	

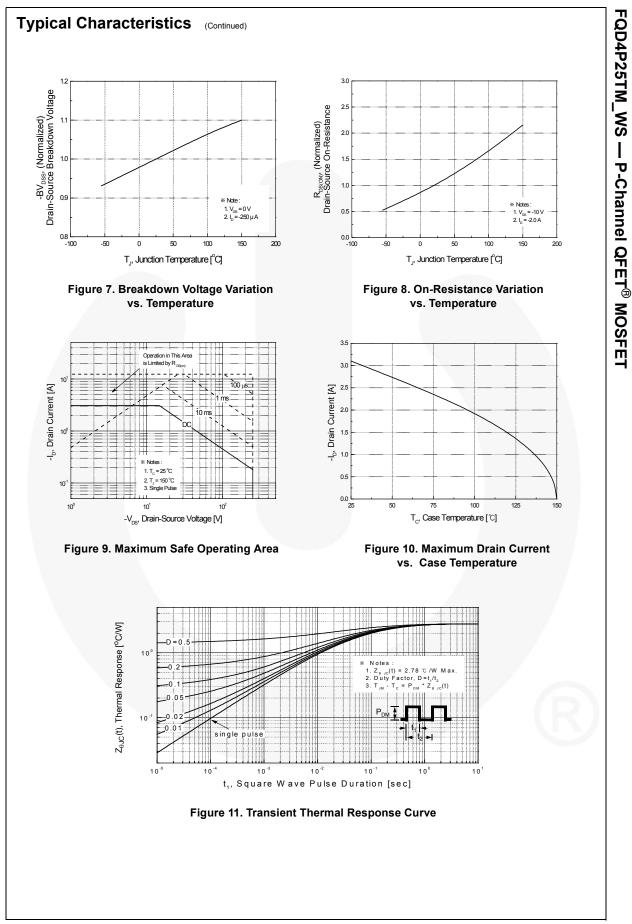
#### **Thermal Characteristics**

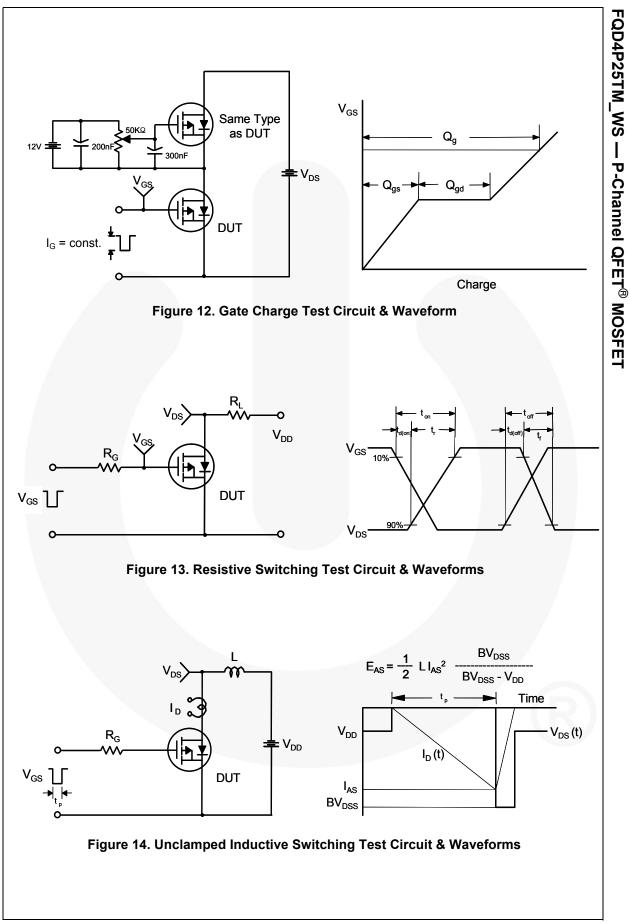
Symbol	Parameter	FQD4P25TM_WS	Unit	
$R_{\thetaJC}$	Thermal Resistance, Junction to Case, Max.	2.78		
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W	
$R_{\theta J A}$	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50		

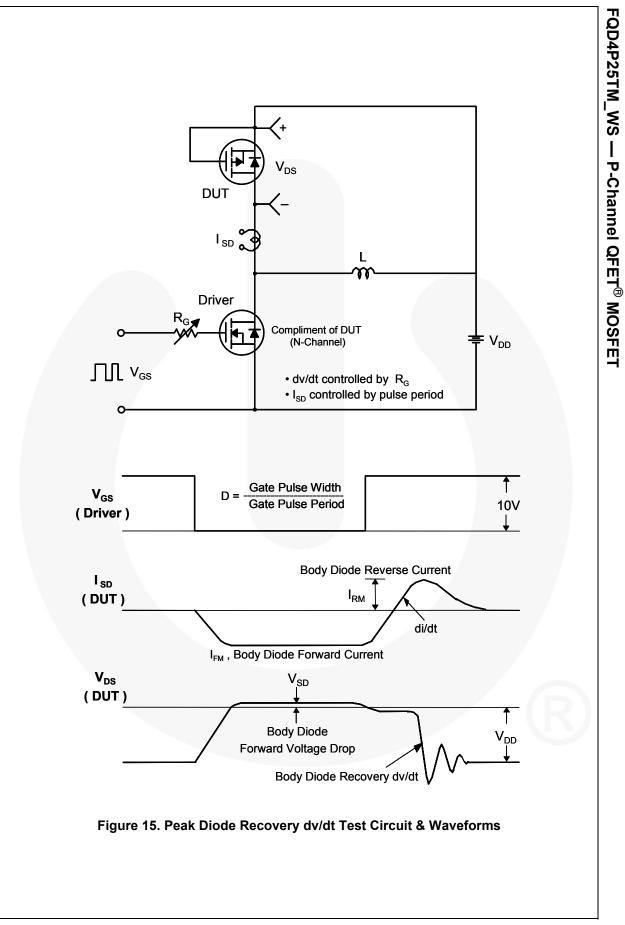
		Top Mark	Pac	ackage Packing Method Reel		d Reel	Size	Tape Width		Quantity	
		DF	DPAK Tape and Reel 330			mm	16 mm		2500 units		
lectri	cal Char	acteristics	T <sub>C</sub> = 25°C	unless oth	erwise noted.						
Symbol		Parameter			Test Conditions		Min.	Тур.	Max.	Unit	
Off Cha	racteristic	`S									
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage		e	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA			-250			V	
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward		;	$I_D = -250 \ \mu$ A, Referenced to 25°C				-0.21		V/°C	
DSS			t -	$V_{DS} = -250 V, V_{GS} = 0 V$ $V_{DS} = -200 V, T_{C} = 125^{\circ}C$ $V_{GS} = -30 V, V_{DS} = 0 V$					-1 -10 -100	μA μA	
GSSF			rward							nA	
GSSR		Leakage Current, Re			30 V, V <sub>DS</sub> = 0 V				100	nA	
	ractorictic	<u> </u>									
Un Cna √ <sub>GS(th)</sub>	Gate Thresh				/ <sub>GS</sub> , I <sub>D</sub> = -250 μA		-3.0		-5.0	V	
R <sub>DS(on)</sub>	Static Drain	-Source			10 V, I <sub>D</sub> = -1.55 A			1.63	2.1	Ω	
ĴFS		insconductance		V <sub>DS</sub> = -	40 V, I <sub>D</sub> = -1.55 A	-		2.0		S	
	c Charact							005	100		
C <sub>iss</sub>	Input Capac			V <sub>DS</sub> = -25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz				325	420	pF	
C <sub>oss</sub> C <sub>rss</sub>	Output Cap	acitance ansfer Capacitance						65 10	85 13	pF pF	
Switchi	ng Charac Turn-On De			Vpp = -	.125 V, I <sub>D</sub> = -4.0 A,			9.5	30	ns	
r	Turn-On Ris	se Time		R <sub>G</sub> = 2				60	130	ns	
d(off)	Turn-Off De	lay Time		0				14	40	ns	
f	Turn-Off Fa	ll Time				(Note 4)		27	65	ns	
כ <sup>g</sup>	Total Gate C	Charge		V <sub>DS</sub> = -200 V, I <sub>D</sub> = -4.0 A, V <sub>GS</sub> = -10 V				10.3	14	nC	
Q <sub>gs</sub>	Gate-Sourc	e Charge						2.7		nC	
ე <sub>gd</sub>	Gate-Drain	Charge				(Note 4)		5.2		nC	
Drain-S	ource Dio	de Characterist	ics an	d Max	imum Ratings						
s	Maximum C	ontinuous Drain-Sou	irce Diod	de Forwa	ard Current				-3.1	Α	
	Maximum P	ulsed Drain-Source I	Diode Fo						-12.4	А	
/ <sub>SD</sub>	Drain-Sourc	e Diode Forward Vol	Itage		0 V, I <sub>S</sub> = -3.1 A				-5.0	V	
	Reverse Re	covery Time			0 V, I <sub>S</sub> = -4.0 A,			140		ns	
כ <sup>ת</sup>	Reverse Re	covery Charge		dI <sub>F</sub> / dt	= 100 A/µs			0.64		μC	
I <sub>S</sub> I <sub>SM</sub> V <sub>SD</sub> t <sub>rr</sub>	Maximum C Maximum P Drain-Sourc Reverse Re	ontinuous Drain-Sou ulsed Drain-Source I e Diode Forward Vol covery Time	irce Dioo Diode Fo	de Forwa prward C V <sub>GS</sub> = ( V <sub>GS</sub> = (	ard Current Current $D V, I_S = -3.1 A$ $D V, I_S = -4.0 A,$	_		  140	-12.4 -5.0 		
<b>×</b> m	Reverse Re	covery Charge		ui <sub>F</sub> / at	- 100 Αγμs			0.64		μC	
L = 46.6 mH I <sub>SD</sub> ≤ -4.0 /	l, I <sub>AS</sub> = -3.1 A, V <sub>D</sub> A, diVdt≤ 300 AVµ	limited by maximum Huncti $_{D}$ = -50V, $R_{G}$ = 25 $\Omega$ , startin s, $V_{DD} \leq BV_{DSS}$ , starting T erating temperature.									

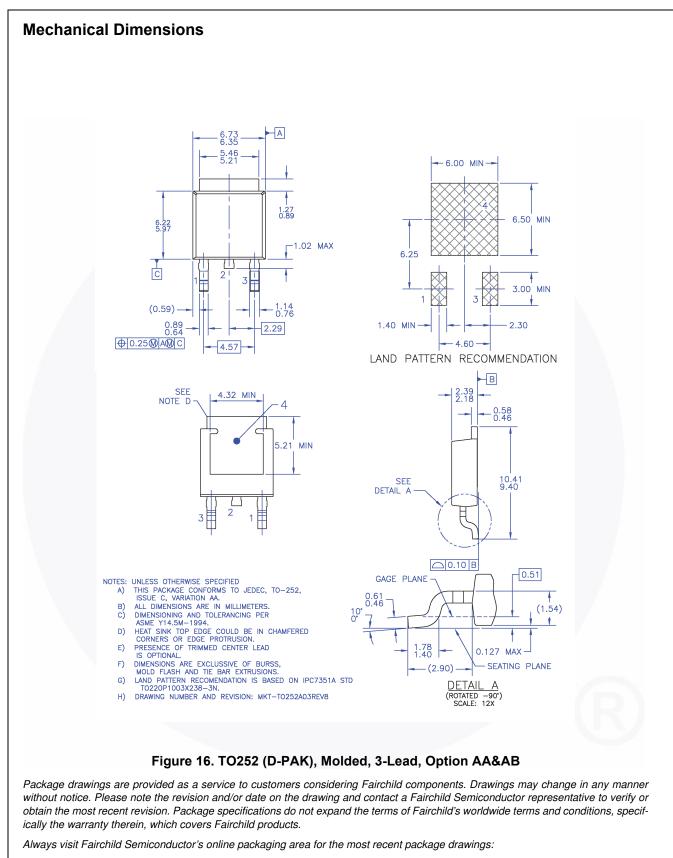
FQD4P25TM\_WS — P-Channel QFET<sup>®</sup> MOSFET











http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT252-003

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Rev. 166

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